



DMN3032LFDBQ

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
30V	30mΩ @ V _{GS} = 10V	6.2A
	$42m\Omega @ V_{GS} = 4.5V$	5.2A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and ideal for use in:

- Body Control Electronics
- Power Management Functions
- DC-DC Converters

D2 D2 G1 S1 Bottom View

U-DFN2020-6

Features and Benefits

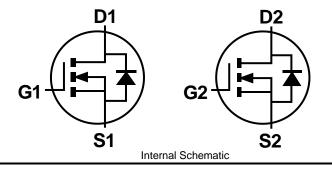
 100% Unclamped Inductive Switching – Ensures More Reliable and Robust Application

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

- Low On-Resistance Minimizes Power Losses
- Low Gate Charge Minimizes Switching Losses
- Small Form Factor Low Profile Package Increased Power Density
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)



Ordering Information (Notes 4 & 5)

Part Number	Case	Packaging
DMN3032LFDBQ-7	U-DFN2020-6	3,000/Tape & Reel
DMN3032LFDBQ-13	U-DFN2020-6	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

	N5	ΥM	
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N5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: C = 2015)

M = Month (ex: 9 = September)

Date Code Key												
Year	201	5	2016		2017	20	18	2019		2020	2	2021
Code	С		D		E		F	G		Н		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	30	V	
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 7) $V_{GS} = 10V$ State $T_A = +25^{\circ}C$ State $T_A = +75^{\circ}C$		ID	6.2 5.0	A	
Maximum Continuous Body Diode Forward Currer	nt (Note 7)		Is	2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	%)	I _{DM}	25	A	
Avalanche Current (Note 8) L = 0.1mH		I _{AS}	12	A	
Avalanche Energy (Note 8) L = 0.1mH		E _{AS}	10	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 6)		PD	1.0	W	
Thermal Desistance, Junction to Ambient (Note 6)	Steady state	P	127	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{ extsf{ heta}JA}$	75		
Total Power Dissipation (Note 7)		PD	1.7	W	
Thermal Pagistance, Junction to Ambient (Note 7)	Steady state	D	72		
Thermal Resistance, Junction to Ambient (Note 7)		$R_{ extsf{ heta}JA}$	43	°C/W	
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	9		
Operating and Storage Temperature Range		T _{J.} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			_					
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 9)								
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$		
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	-	-	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$		
Zero Gate Voltage Drain Current $T_J = +150^{\circ}C$ (Note 10)	I _{DSS}	-	-	100	μA	$V_{DS} = 30V, V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 9)								
Gate Threshold Voltage	V _{GS(TH)}	1.0	1.5	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$		
Static Drain-Source On-Resistance			25	30	mΩ	$V_{GS} = 10V, I_D = 5.8A$		
	R _{DS(ON)}	-	30	42	11152	$V_{GS} = 4.5V, I_D = 4.8A$		
Diode Forward Voltage	V _{SD}	-	0.75	1.2	V	$V_{GS} = 0V, I_S = 1A$		
DYNAMIC CHARACTERISTICS (Note 10)								
Input Capacitance	Ciss	-	500	-	pF			
Output Capacitance	Coss	-	52	-	pF	− V _{DS} = 15V, V _{GS} = 0V, − f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}	-	44	-	pF	1 = 1.00012		
Gate Resistance	Rg	-	2.3	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$		
Total Gate Charge ($V_{GS} = 4.5V$)	Qg	-	5.0	-	nC			
Total Gate Charge (V _{GS} = 10V)	Qg	-	10.6	-	nC	V _{DS} = 15V, I _D = 5.8A		
Gate-Source Charge	Q _{gs}	-	1.3	-	nC	$v_{DS} = 15v, I_D = 5.6A$		
Gate-Drain Charge	Q _{gd}	-	1.8	-	nC			
Turn-On Delay Time	t _{D(ON)}	-	2.2	-	ns			
Turn-On Rise Time	t _R	-	2.6	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$		
Turn-Off Delay Time	t _{D(OFF)}	-	9.7	-	ns	$R_L = 2.6\Omega, R_G = 3\Omega$		
Turn-Off Fall Time	tF	-	2.0	-	ns			

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

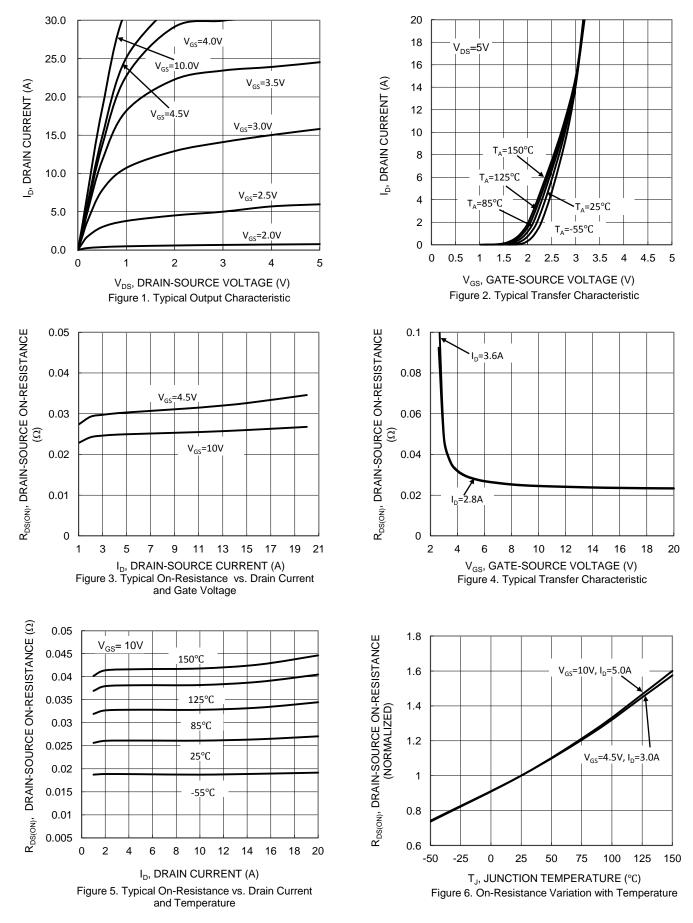
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

9. Short duration pulse test used to minimize self-heating effect.

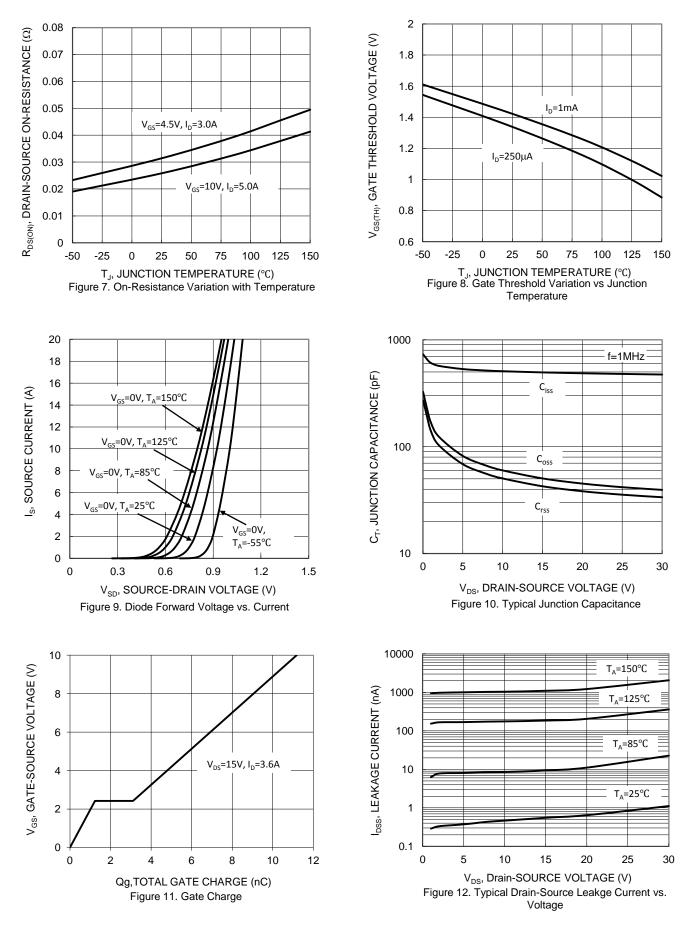
10. Guaranteed by design. Not subject to product testing.



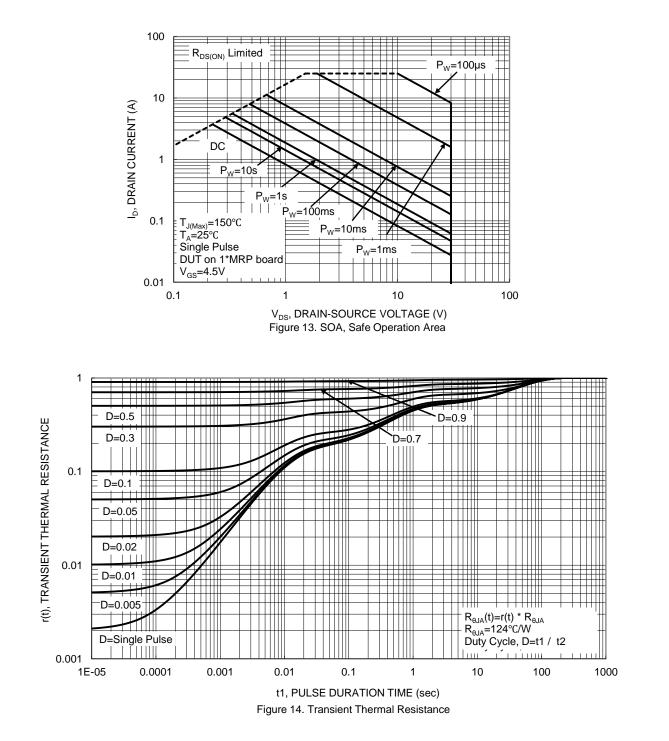


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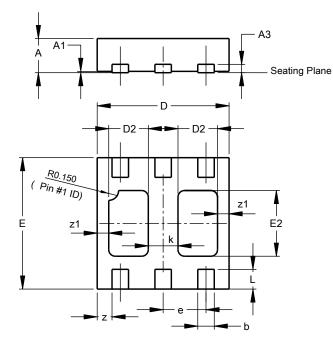






Package Outline Dimensions

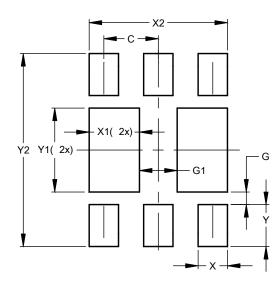
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2020-6 Type B							
Dim	Min						
Α	0.545	0.605	0.575				
A1	0.00	0.05	0.02				
A3	-	-	0.13				
b	0.20	0.30	0.25				
D	1.95	2.075	2.00				
D2	0.50	0.70	0.60				
е	-	-	0.65				
Е	1.95	2.075	2.00				
E2	0.90	1.10	1.00				
k	-	-	0.45				
L	0.25	0.35	0.30				
z	-	-	0.225				
z1	-	-	0.15				
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value
Dimensions	(in mm)
С	0.650
G	0.150
G1	0.450
Х	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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